# SILICON POWER TRANSISTOR 2SA1742

# PNP SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SA1742 is a power transistor developed for high-speed switching and features a high hre at low  $V_{CE(sat)}$ . This transistor is ideal for use as a driver in DC/DC converters and actuators.

In addition, a small resin-molded insulation type package contributes to high-density mounting and reduction of mounting cost.

### FEATURES

NEC

- High hFE and low VCE(sat): hFE ≥ 100 MIN. @VCE = -2.0 V, IC = -1.5 A VCE(sat) ≥ -0.3 V MAX. @IC = -4.0 V, IB = -0.2 A
- Full-mold package that does not require an insulating board or bushing

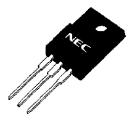
#### Parameter Symbol Conditions Ratings Unit -100 ٧ Collector to base voltage Vсво -60 v Collector to emitter voltage VCEO -7.0 V Emitter to base voltage Vево -7.0 Collector current (DC) IC(DC) А $\overline{PW} \le 300 \ \mu s$ , Collector current (pulse) -14 А C(pulse) duty cycle $\leq 10\%$ -3.5 A Base current (DC) B(DC) Total power dissipation Pτ Tc = 25°C 30 W T<sub>A</sub> = 25°C 2.0 W °C Junction temperature Tj 150 Storage temperature Tstg -55 to +150 °C

#### ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

### **ORDERING INFORMATION**

Part No.	Package
2SA1742	Isolated TO-220

#### (Isolated TO-220)



The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

# ELECTRICAL CHARACTERISTICS (TA = 25°C)

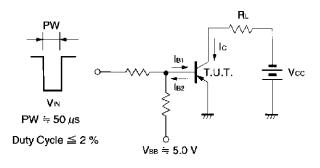
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector to emitter voltage	VCEO(SUS)	Ic = −4.0 V, I <sub>B</sub> = −0.4 A, L = 1 mH	-60			V
	VCEX(SUS)	Ic = -4.0 A, I <sub>B1</sub> = -I <sub>B2</sub> = -0.4 A, V <sub>BE(OFF)</sub> = 1.5 V, L = 180 $\mu$ H, clamped	-60			V
Collector cutoff current	Ісво	$V_{CB} = -60 \text{ V}, \text{ I}_{E} = 0 \text{ A}$			-10	μA
	ICER	$V_{CE} = -60 \text{ V}, \text{ R}_{BE} = 50 \Omega, \text{ T}_{A} = 125^{\circ}\text{C}$			-1.0	mA
	ICEX1	$V_{\text{CE}} = -60 \text{ V}, \text{ V}_{\text{BE(OFF)}} = 1.5 \text{ V}$			-10	μA
	ICEX2	$\label{eq:Vce} \begin{split} V_{\text{CE}} &= -60 \ V, \ V_{\text{BE}(\text{OFF})} = 1.5 \ V, \\ T_{\text{A}} &= 125^{\circ}\text{C} \end{split}$			-1.0	mA
Emitter cutoff current	Іево	$V_{EB} = -5.0 \text{ V}, \text{ Ic} = 0 \text{ A}$			-10	μA
DC current gain	h <sub>FE1</sub>	$V_{CE} = -2.0 \text{ V}, \text{ Ic} = -0.7 \text{ A}^{Note}$	100			
	hfe2	$V_{CE} = -2.0 \text{ V}, \text{ Ic} = -1.5 \text{ A}^{Note}$	100		400	
	hfe3	$V_{CE} = -2.0 \text{ V}, \text{ Ic} = -4.0 \text{ A}^{Note}$	60			
Collector saturation voltage	VCE(sat)1	$I_{C} = -4.0 \text{ A}, I_{B} = -0.2 \text{ A}^{Note}$			-0.3	V
	VCE(sat)2	$I_{C} = -6.0 \text{ A}, I_{B} = -0.3 \text{ A}^{Note}$			-0.5	V
Base saturation voltage	VBE(sat)1	$Ic = -4.0 A$ , $I_B = -0.2 A^{Note}$			-1.2	V
	VBE(sat)2	$I_{C} = -6.0 \text{ A}, I_{B} = -0.3 \text{ A}^{Note}$			-1.5	V
Collector capacitance	Cob	$V_{CB} = -10 \text{ V}, \text{ I}_{E} = 0 \text{ A}, \text{ f} = 1.0 \text{ MHz}$		180		pF
Gain bandwidth product	f⊤	Vcb = -10 V, lc = -1.0 A		40		MHz
Turn-on time	ton	lc = −4.0 A, RL = 12.5 Ω,			0.3	μs
Storage time	tstg	$I_{B1} = -I_{B2} = -0.2 \text{ A}, \text{ Vcc} \cong -50 \text{ V}$			1.5	μs
Fall time	tr	Refer to the test circuit.			0.3	μs

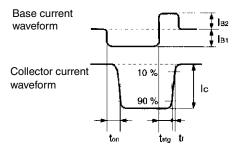
**Note** Pulse test PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2%

#### **hfe CLASSIFICATION**

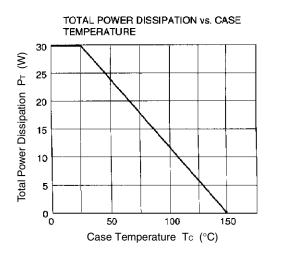
Marking	М	L	К
hfe2	100 to 200	150 to 300	200 to 400

# SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT

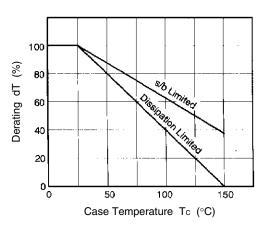




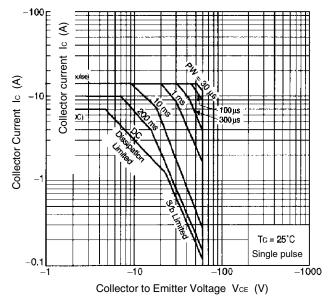




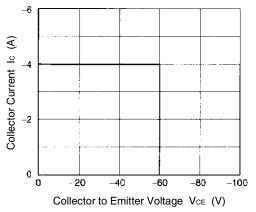
DERATING CURVE OF SAFE OPERATING AREA



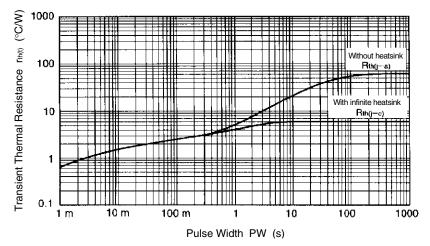
FORWARD BIAS SAFE OPERATING AREA

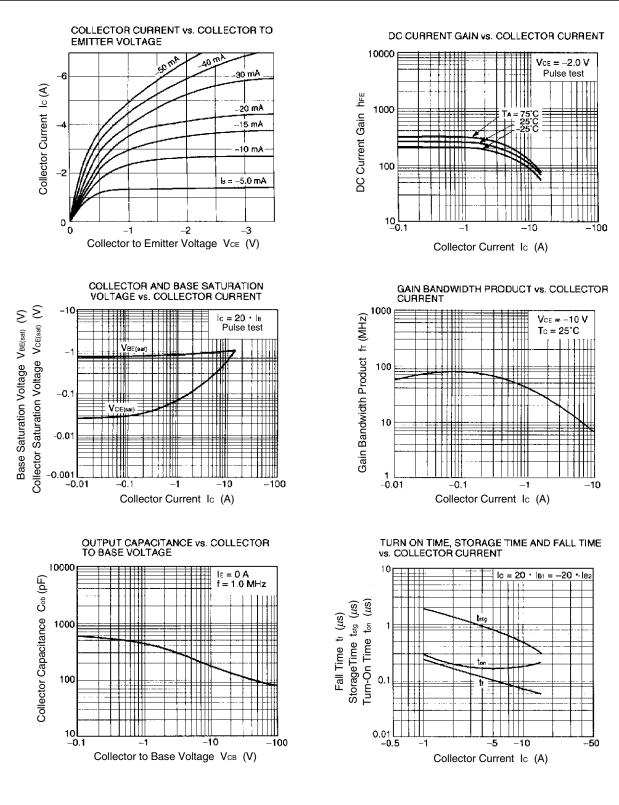


REVERSE BIAS SAFE OPERATING AREA



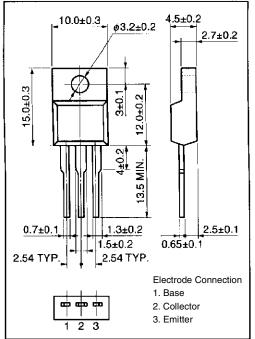
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH





# PACKAGE DRAWING (UNIT: mm)





- The information in this document is current as of July, 2001. The information is subject to change
  without notice. For actual design-in, refer to the latest publications of NEC's data sheets or data
  books, etc., for the most up-to-date specifications of NEC semiconductor products. Not all products
  and/or types are available in every country. Please check with an NEC sales representative for
  availability and additional information.
- No part of this document may be copied or reproduced in any form or by any means without prior written consent of NEC. NEC assumes no responsibility for any errors that may appear in this document.
- NEC does not assume any liability for infringement of patents, copyrights or other intellectual property rights of third parties by or arising from the use of NEC semiconductor products listed in this document or any other liability arising from the use of such products. No license, express, implied or otherwise, is granted under any patents, copyrights or other intellectual property rights of NEC or others.
- Descriptions of circuits, software and other related information in this document are provided for illustrative
  purposes in semiconductor product operation and application examples. The incorporation of these
  circuits, software and information in the design of customer's equipment shall be done under the full
  responsibility of customer. NEC assumes no responsibility for any losses incurred by customers or third
  parties arising from the use of these circuits, software and information.
- While NEC endeavours to enhance the quality, reliability and safety of NEC semiconductor products, customers
  agree and acknowledge that the possibility of defects thereof cannot be eliminated entirely. To minimize
  risks of damage to property or injury (including death) to persons arising from defects in NEC
  semiconductor products, customers must incorporate sufficient safety measures in their design, such as
  redundancy, fire-containment, and anti-failure features.
- NEC semiconductor products are classified into the following three quality grades:
   "Standard", "Special" and "Specific". The "Specific" quality grade applies only to semiconductor products
   developed based on a customer-designated "quality assurance program" for a specific application. The
   recommended applications of a semiconductor product depend on its quality grade, as indicated below.
   Customers must check the quality grade of each semiconductor product before using it in a particular
   application.
  - "Standard": Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
  - "Special": Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
  - "Specific": Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems and medical equipment for life support, etc.

The quality grade of NEC semiconductor products is "Standard" unless otherwise expressly specified in NEC's data sheets or data books, etc. If customers wish to use NEC semiconductor products in applications not intended by NEC, they must contact an NEC sales representative in advance to determine NEC's willingness to support a given application.

(Note)

- (1) "NEC" as used in this statement means NEC Corporation and also includes its majority-owned subsidiaries.
- (2) "NEC semiconductor products" means any semiconductor product developed or manufactured by or for NEC (as defined above).